

MB98A608A-25/609A-25/610A-25 EPROM MEMORY CARD

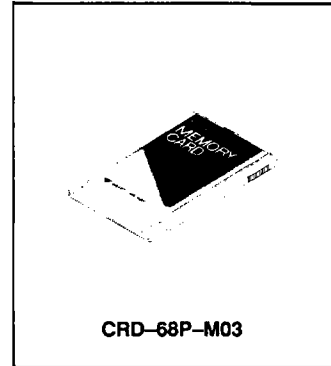
UV ERASABLE READ ONLY MEMORY CARD 256K/512K/1M-BYTE

The Fujitsu MB98A608A, MB98A609A and MB98A610A are UV Erasable Read Only Memory (EPROM) cards capable of storing and retrieving large amounts of data. Each EPROM card contains multiple MBM27C1001 devices.

The EPROM memory circuits are housed in a credit-card sized 68-pin package. Internal circuitry is protected by metal plates on the top and bottom of the card to help reduce chip damage from electro-static discharge.

A unique feature of the Fujitsu memory cards allows the user to organize the card into either an 8-bit or a 16-bit organization. All cards are portable and operate at high speed with low power needs.

- Card Dimensions: 85.6 length x 54.0 width x 4.05 thickness (mm)
- Connector Type: Two-piece 68-pin (Built-in 68-pin receptacle, 2-row type)
- Complete static operation: No clock required
- TTL compatible inputs/outputs
- Three-state outputs
- Single + 5.0 V \pm 5% power supply



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AVAILABLE ORGANIZATIONS

Part Number	Mounted Memory Device	Access Time	Memory Organization *
MB98A608A-25	MBM27C1001 x 2 pcs	250 ns	256K x 8 bits/128K x 16 bits
MB98A609A-25	MBM27C1001 x 4 pcs	250 ns	512K x 8 bits/256K x 16 bits
MB98A610A-25	MBM27C1001 x 8 pcs	250 ns	1 M x 8 bits/512K x 16 bits

* To be configured by user.

ABSOLUTE MAXIMUM RATINGS (see NOTE.)

Rating	Symbol	Value	Unit
Supply Voltage	V _{CC}	-0.3 to +7.0	V
Input Voltage	V _{IN}	-0.5 to V _{CC} +0.5	V
Output Voltage	V _{IO}	-0.5 to V _{CC} +0.5	V
Programming Voltage	V _{CC} /V _{PP1} , V _{CC} /V _{PP2}	-0.5 to +13.5	V
Temperature under Bias	T _{BIAS}	-10 to +60	°C
Storage Temperature	T _{STG}	-30 to +70	°C

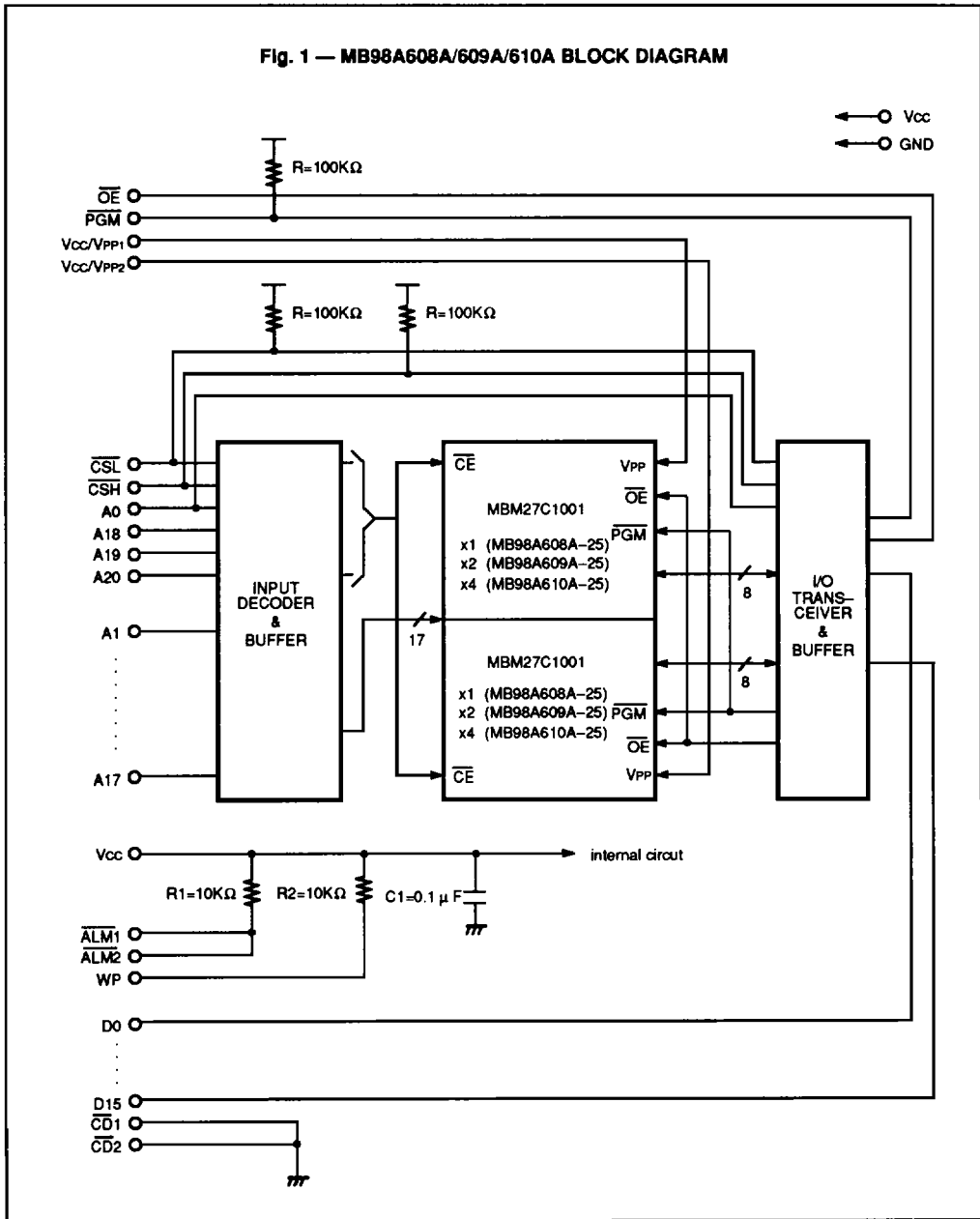
NOTE: Permanent device damage may occur if the above **Absolute Maximum Ratings** are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

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Fig. 1 — MB98A608A/609A/610A BLOCK DIAGRAM



PIN DESCRIPTION

Symbol	Pin Name	Input/Output	Function
A0 to A20	Address Input	Input	Address Inputs, A0–A20
D0 to D15	Data Input/Output	Input/Output	Data Inputs/Outputs This data bus size (8-bit or 16-bit) selected with $\overline{\text{CSL}}$ and $\overline{\text{CSH}}$.
$\overline{\text{CSL}}$	Chip Select for Lower Byte	Input	Active Low –Lower byte (D0–D7) is selected for read/write function. (Refer to FUNCTION TRUTH TABLE.)
$\overline{\text{CSH}}$	Chip Select for Upper Byte	Input	Active Low –Upper byte (D8–D15) is selected for read/write function. (Refer to FUNCTION TRUTH TABLE.)
$\overline{\text{OE}}$	Output Enable	Input	Active Low –Output enable for EPROM cards
$\overline{\text{PGM}}$	Programming Enable	Input	Active Low –Programming enable for EPROM cards
Vcc/VPP1	Power Supply/Programming Voltage 1	Input	Vcc –Power supply voltage for lower byte Active VPP –Programming voltage for lower byte
Vcc/VPP2	Power Supply/Programming Voltage 2	Input	Vcc –Power supply voltage for upper byte Active VPP –Programming voltage for upper byte
$\overline{\text{CD}}1, \overline{\text{CD}}2$	Card Detect	Output	These pins detect if the card has been correctly inserted. Both pins are tied to GND internally.
WP	Write Protect	Output	This pin outputs high level for programmed OTP ROM cards and low level for blank cards.
$\overline{\text{ALM}}1, \overline{\text{ALM}}2$	Battery Alarm	Output	Both pins are tied to Vcc internally.
Vcc	Power Supply	–	Power Supply Voltage (+5.0V ±5%)
GND	Ground	–	System Ground
NC	Non Connection	–	

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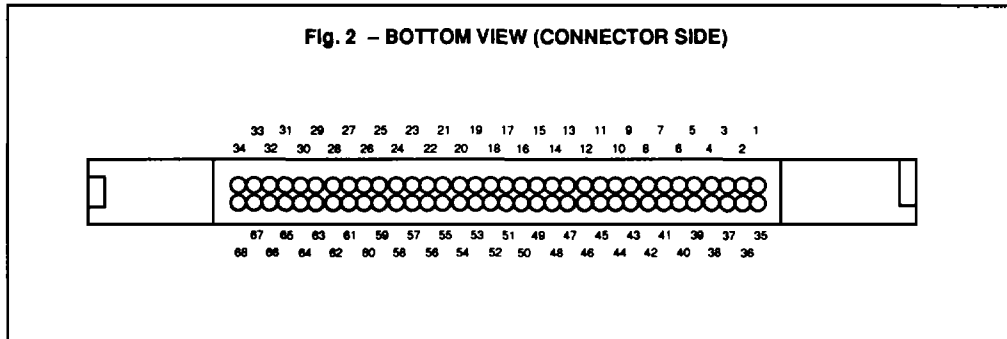
PIN ASSIGNMENTS

MB98A608A	MB98A609A	MB98A610A	Pin No.		MB98A608A	MB98A609A	MB98A610A
GND	GND	GND	1	35	GND	GND	GND
D3	D3	D3	2	36	$\overline{CD}1$	$\overline{CD}1$	$\overline{CD}1$
D4	D4	D4	3	37	D11	D11	D11
D5	D5	D5	4	38	D12	D12	D12
D6	D6	D6	5	39	D13	D13	D13
D7	D7	D7	6	40	D14	D14	D14
\overline{CSL}	\overline{CSL}	\overline{CSL}	7	41	D15	D15	D15
A10	A10	A10	8	42	\overline{CSH}	\overline{CSH}	\overline{CSH}
\overline{OE}	\overline{OE}	\overline{OE}	9	43	NC	NC	NC
A11	A11	A11	10	44	NC	NC	NC
A9	A9	A9	11	45	NC	NC	NC
A8	A8	A8	12	46	A17	A17	A17
A13	A13	A13	13	47	A18 *	A18	A18
A14	A14	A14	14	48	A19 *	A19 *	A19
\overline{PGM}	\overline{PGM}	\overline{PGM}	15	49	A20 *	A20 *	A20 *
NC	NC	NC	16	50	NC	NC	NC
Vcc	Vcc	Vcc	17	51	Vcc	Vcc	Vcc
Vcc/VPP1	Vcc/VPP1	Vcc/VPP1	18	52	Vcc/VPP2	Vcc/VPP2	Vcc/VPP2
A16	A16	A16	19	53	NC	NC	NC
A15	A15	A15	20	54	NC	NC	NC
A12	A12	A12	21	55	NC	NC	NC
A7	A7	A7	22	56	NC	NC	NC
A6	A6	A6	23	57	NC	NC	NC
A5	A5	A5	24	58	NC	NC	NC
A4	A4	A4	25	59	NC	NC	NC
A3	A3	A3	26	60	NC	NC	NC
A2	A2	A2	27	61	NC	NC	NC
A1	A1	A1	28	62	$\overline{ALM}1$	$\overline{ALM}1$	$\overline{ALM}1$
A0	A0	A0	29	63	$\overline{ALM}2$	$\overline{ALM}2$	$\overline{ALM}2$
D0	D0	D0	30	64	D8	D8	D8
D1	D1	D1	31	65	D9	D9	D9
D2	D2	D2	32	66	D10	D10	D10
WP	WP	WP	33	67	$\overline{CD}2$	$\overline{CD}2$	$\overline{CD}2$
GND	GND	GND	34	68	GND	GND	GND

Note: A18, A19 and A20 pins asterisked "*" are non connection.

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PIN LOCATIONS



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FUNCTION TRUTH TABLE

$\overline{\text{CSH}}$	$\overline{\text{CSL}}$	A0	$\overline{\text{OE}}$	$\overline{\text{PGM}}$	Vcc/Vpp1	Vcc/Vpp2	Mode	Data Input/Output	
								D15–D8	D7–D0
H	H	X	X	X	5 V	5 V	Standby	High-Z	
H	L	L	L	H	5 V	5 V	Read (x8)	High-Z	DOUT (Lower Byte)
H	L	H	L	H	5 V	5 V	Read (x8)	High-Z	DOUT (Upper Byte)
H	L	L	H	L	6 V	12.5 V	Write (x8)	High-Z	DIN (Lower Byte)
H	L	H	H	L	12.5 V	6 V	Write (x8)	High-Z	DIN (Upper Byte)
L	H	X	H	L	12.5 V	6 V	Write (x8)	DIN (Upper Byte)	High-Z
L	H	X	L	H	5 V	5 V	Read (x8)	DOUT (Upper Byte)	High-Z
L	L	X	L	H	5 V	5 V	Read (x16)	DOUT	
L	L	X	H	L	12.5 V	12.5 V	Write (x16)	DIN	
X	X	X	H	L	5 V	5 V	Output Disable	High-Z	

Definition: H = VH, L = VL, X = Either VL or VH

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ADDRESS CONFIGURATION USING 8-BIT BUS ($\overline{CSH} = H, \overline{CSL} = L$)

A20 to A0						\overline{CSH}	\overline{CSL}	D15-D8	D7-D0
0	0000	0000	0000	0000	0000	H	L	High-Z	0 Add.
0	0000	0000	0000	0000	0001	H	L	High-Z	1 Add.
0	0000	0000	0000	0000	0010	H	L	High-Z	2 Add.
0	0000	0000	0000	0000	0011	H	L	High-Z	3 Add.
↓	↓	↓	↓	↓	↓	↓	↓	↓ ↓	↓ ↓
1	1111	1111	1111	1111	1100	H	L	High-Z	2097148 Add.
1	1111	1111	1111	1111	1101	H	L	High-Z	2097149 Add.
1	1111	1111	1111	1111	1110	H	L	High-Z	2097150 Add.
1	1111	1111	1111	1111	1111	H	L	High-Z	2097151 Add.

ADDRESS CONFIGURATION USING 8-BIT BUS ($\overline{CSH} = L, \overline{CSL} = H$)

A20 to A0						\overline{CSH}	\overline{CSL}	D15-D8	D7-D0
0	0000	0000	0000	0000	000X	L	H	1 Add.	High-Z
0	0000	0000	0000	0000	001X	L	H	3 Add.	High-Z
0	0000	0000	0000	0000	010X	L	H	5 Add.	High-Z
0	0000	0000	0000	0000	011X	L	H	7 Add.	High-Z
↓	↓	↓	↓	↓	↓	↓	↓	↓ ↓	↓ ↓
1	1111	1111	1111	1111	100X	L	H	2097145 Add.	High-Z
1	1111	1111	1111	1111	101X	L	H	2097147 Add.	High-Z
1	1111	1111	1111	1111	110X	L	H	2097149 Add.	High-Z
1	1111	1111	1111	1111	111X	L	H	2097151 Add.	High-Z

Definition: X = Either "0" or "1". Even addresses are not available in this mode.

ADDRESS CONFIGURATION USING 16-BIT BUS ($\overline{CSH} = L, \overline{CSL} = L$)

A20 to A0						\overline{CSH}	\overline{CSL}	D15-D8	D7-D0
0	0000	0000	0000	0000	000X	L	L	1 Add.	0 Add.
0	0000	0000	0000	0000	001X	L	L	3 Add.	2 Add.
0	0000	0000	0000	0000	010X	L	L	5 Add.	4 Add.
0	0000	0000	0000	0000	011X	L	L	7 Add.	6 Add.
↓	↓	↓	↓	↓	↓	↓	↓	↓ ↓	↓ ↓
1	1111	1111	1111	1111	100X	L	L	2097145 Add.	2097144 Add.
1	1111	1111	1111	1111	101X	L	L	2097147 Add.	2097146 Add.
1	1111	1111	1111	1111	110X	L	L	2097149 Add.	2097148 Add.
1	1111	1111	1111	1111	111X	L	L	2097151 Add.	2097150 Add.

Definition: X = Either "0" or "1".

RECOMMENDED OPERATING CONDITIONS

(Referenced to GND)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V _{CC}	4.75	5.0	5.25	V
Programming Voltage during Read Mode	V _{PP}	V _{CC} -0.6	V _{CC}	V _{CC} +0.6	V
Input High Voltage	V _{IH}	2.4		V _{CC} +0.3	V
Input Low Voltage	V _{IL}	-0.1		0.8	V
Ambient Temperature	T _A	0		50	°C

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DC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

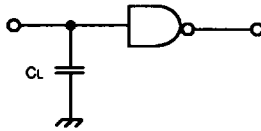
Parameter	Test Condition	Symbol	Min	Max	Unit
Standby Supply Current	$\overline{CSL}=\overline{CSH}\geq V_{CC}-0.2V$	I _{SB1}		100	μA
	$\overline{CSL}=\overline{CSH}=V_{IH}$	I _{SB2}		10	mA
Active Supply Current	V _{IN} =V _{IH} or V _{IL} CSL=CSH=V _{IL} , I _{OUT} =0mA	I _{CC1}		100	mA
Operating Supply Current	Cycle=Min. Duty=100%, I _{OUT} =0mA	I _{CC2}		100	mA
Input Leakage Current (except \overline{CSL} , \overline{CSH} , \overline{PGM})	V _{IN} =0V or V _{CC}	I _{LI}	-10	10	μA
Output Leakage Current (except $\overline{ALM1}$, $\overline{ALM2}$, WP, $\overline{CD1}$, $\overline{CD2}$)	V _{OUT} =0V or V _{CC} CSL=CSH=V _{IH} OE=V _{IH} or $\overline{PGM}=V_{IL}$	I _{LVO}	-10	10	μA
Output High Voltage (except $\overline{ALM1}$, $\overline{ALM2}$, WP)	V _{OH} =-1.0mA	V _{OH}	2.4		V
Output Low Voltage (except $\overline{CD1}$, $\overline{CD2}$)	V _{OL} =2.1mA	V _{OL}		0.4	V

Note: All voltages are referenced to GND.

CAPACITANCE (T_A=25°C, f=1MHz, V_{IN}=V_{I/O}=GND)

Parameter	Symbol	Min	Typ	Max	Unit
Input Capacitance (except \overline{CSL} , \overline{CSH} , \overline{PGM})	C _{IN}			50	pF
I/O Capacitance (except $\overline{ALM1}$, $\overline{ALM2}$, WP, $\overline{CD1}$, $\overline{CD2}$)	C _{OUT}			50	pF

Fig. 3 – AC TEST CONDITIONS



- Input Pulse Levels: 0.6V to 2.6V
- Input Pulse Rise & Fall Times: $t_T = 5\text{ns}$ (Transient between 0.8V and 2.4V)
- Timing Reference Levels
 - Input: $V_{IL} = 0.8\text{V}$, $V_{IH} = 2.4\text{V}$
 - Output: $V_{OL} = 0.8\text{V}$, $V_{OH} = 2.0\text{V}$
- Output Load: 1TTL gate + C_L (100pF)

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AC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

READ CYCLE

Parameter	Symbol	Min	Max	Unit
Address Access Time * ₁	t_{ACC}		250	ns
Chip Select Access Time	t_{CS}		250	ns
Output Enable to Output Valid * ₁	t_{OE}		120	ns
Output Disable Time * ₂	t_{DF}		100	ns
Output Hold Time	t_{OH}	0		ns

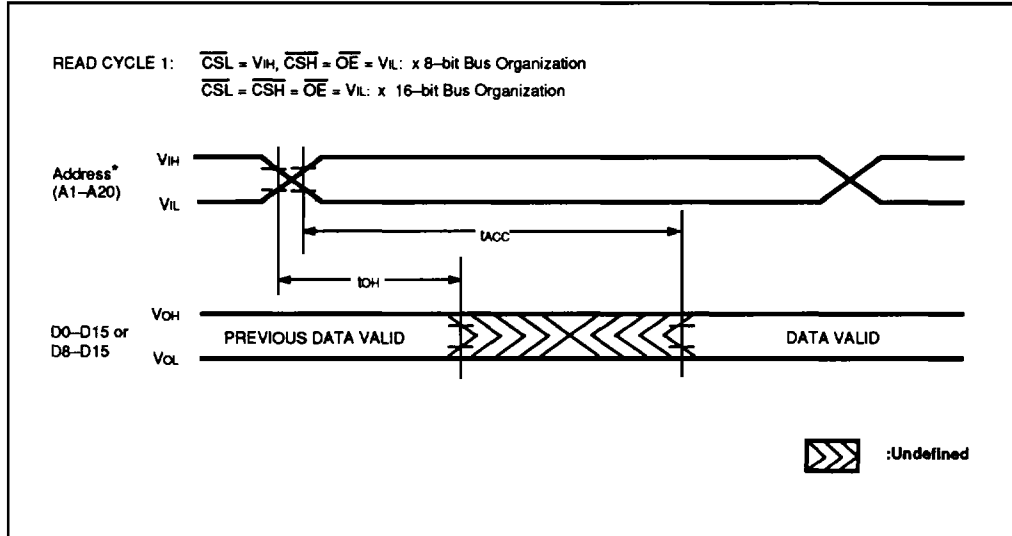
Note: *₁ t_{OE} may be delayed up to $t_{ACC} - t_{OE}$ after the falling edge of \overline{CSL} , \overline{CSH} without impact on t_{ACC} .

*₂ t_{DF} is specified from the rising edge of \overline{OE} , \overline{CSL} or \overline{CSH} , whichever occurs first.
 Output Float is defined as the point where data is no longer driven.

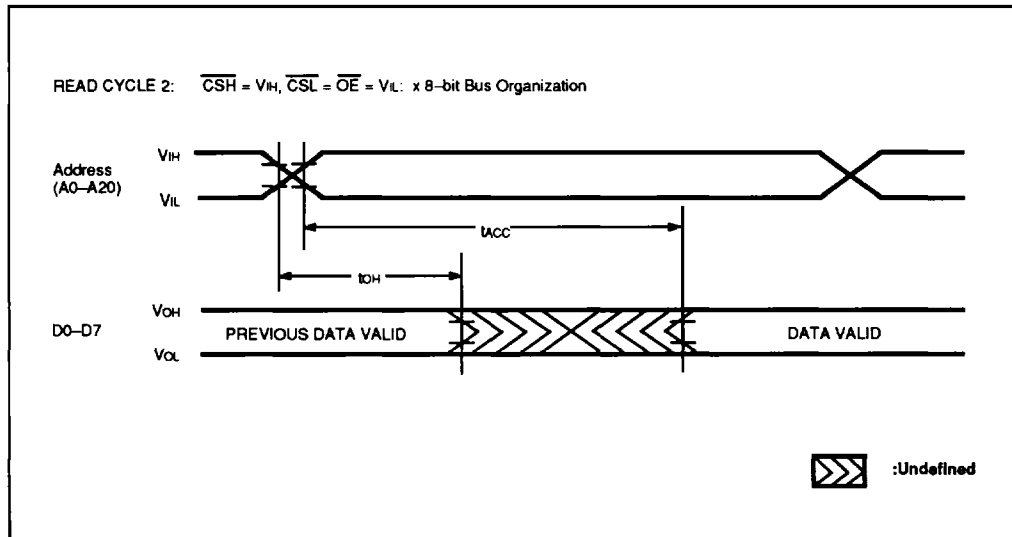
AC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

READ CYCLE TIMING DIAGRAM ($\overline{\text{PGM}} = \text{V}_{\text{IH}}$)



Note: * A0 = Either V_{L} or V_{IH} .



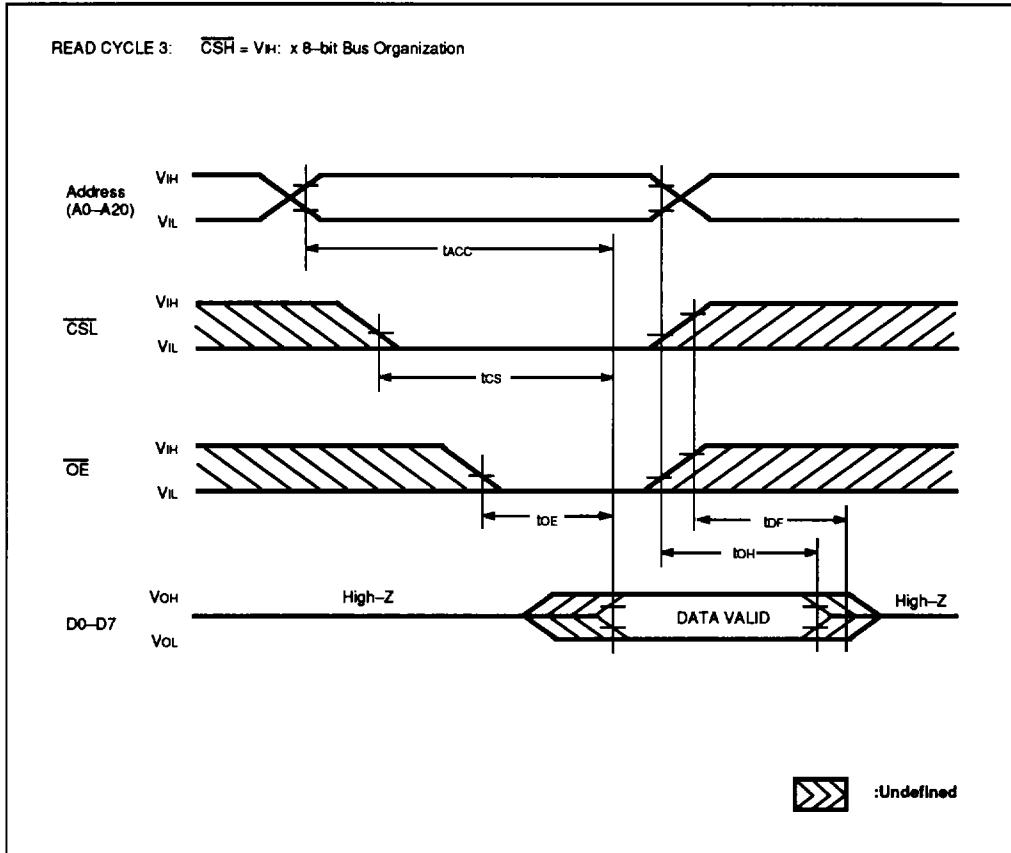
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AC CHARACTERISTICS (Continued)

(Recommended operating conditions unless otherwise noted.)

READ CYCLE TIMING DIAGRAM ($\overline{\text{PGM}} = \text{V}_{\text{IH}}$)

READ CYCLE 3: $\overline{\text{CSH}} = \text{V}_{\text{IH}}$; x 8-bit Bus Organization

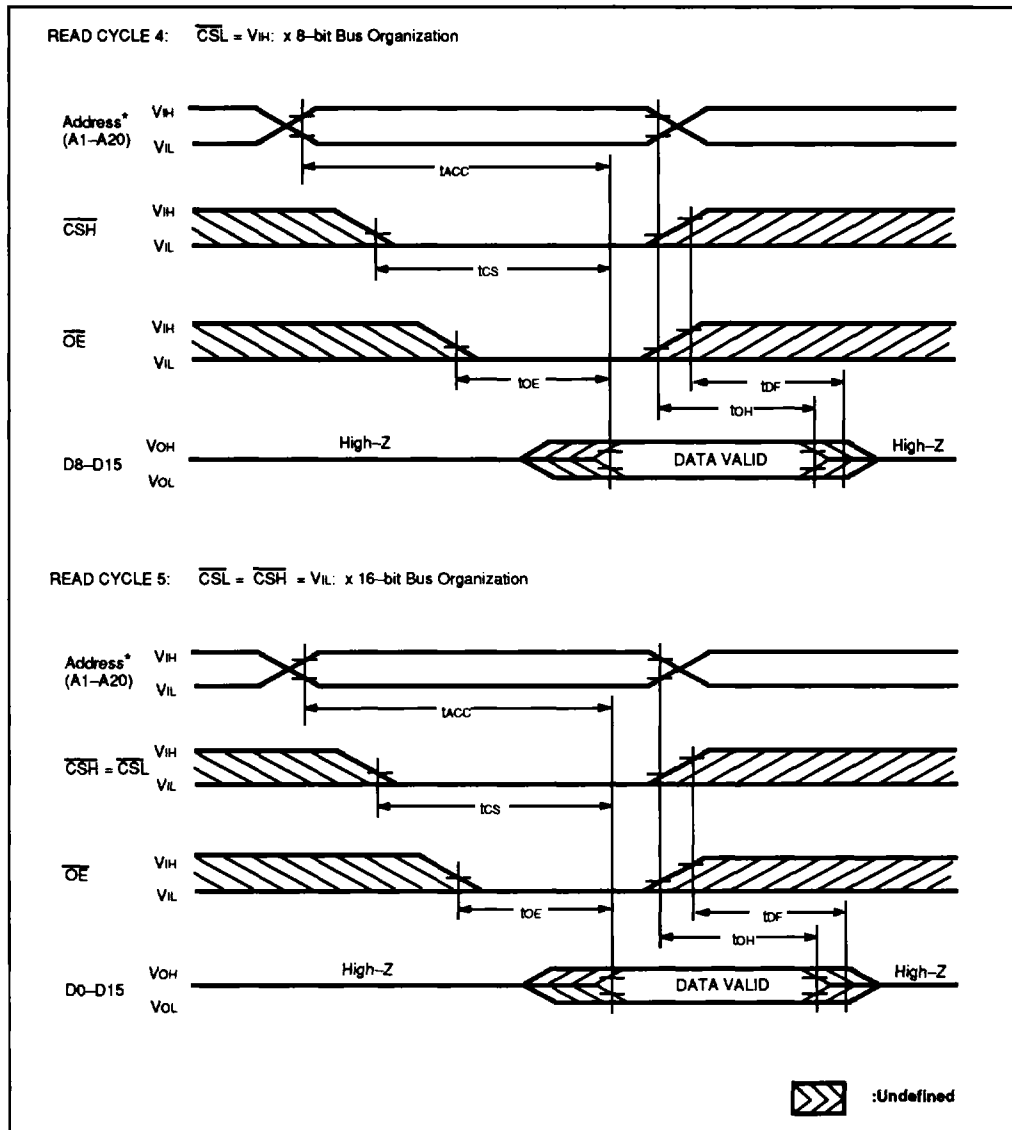


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AC CHARACTERISTICS (Continued)

(Recommended operating conditions unless otherwise noted.)

READ CYCLE TIMING DIAGRAM ($\overline{\text{PGM}} = V_{\text{IH}}$)



Note: * A0 = Either V_{IL} or V_{IH} .

PROGRAMMING/ERASING INFORMATION

PROGRAMMING

When the MB98A608A/609A/610A is shipped from the factory, all memory cells are set to the high state (logic 1). During the programming procedure, affected bit cells are set to the low state (logic 0).

1 When +12.5(±0.3) volts is applied to VPP, +6(±0.25) volts is applied to Vcc, CSL (CSH)=VIL, OE and PGM=VIH, the programming mode is initiated. Next, the proper address is input and the data pattern is applied to the input buffer. After both the address and data are stable, a 0.5-millisecond negative pulse is applied to the PGM pin. Upon verification of written data an over pulse (three times the initial pulse width times the number of pulse used to accomplish a write) should be applied to OE complete word. Refer to the PROGRAMMING FLOWCHART that follows for step-by-step programming procedures.

CAUTION

A TTL low-level voltage should not be applied to the PGM pin during the programming mode (VPP=+12.5 volts). Also, the VPP voltage must not be switched from Vcc to +12.5 volts or vice-versa. Neglecting either of these precautions may cause device failure.

ELECTRONIC SIGNATURE

The MB98A608A/609A/610A has no electronic signature code. Therefore, more than +6 volts should not be applied to A9 pin.

ERASING

In order to clear all memory cells of programmed contents, the MB98A608A/609A/610A must be exposed to an ultraviolet light source after taking off the cover of this card. To completely erase the memory (restore all cells to a logic 1 state), a dosage of 10Wsec/cm² is required. The required exposure can be obtained by using a UV-lamp with a wavelength of 2537 Angstroms and with an intensity of 12mW/cm². Remove all filters from the lamp and clean the transparent lid of the MB98A6xxA approximately one inch from the light source for 20-to-25 minutes.

PROGRAMMING INFORMATION (Continued)
DC CHARACTERISTICS (TA=25°C, VCC¹=6V±0.25V, VPP²=12.5V±0.5V)

Parameter	Test Condition	Symbol	Min	Max	Unit
Input Leakage Current		I _{LI}		10	μA
VPP Supply Current during Programing	$\overline{CSL}=\overline{CSH}=V_L$ $\overline{OE}=V_{IH}, \overline{PGM}=V_{IL}$ $\overline{OE}/V_{PP1}=\overline{OE}/V_{PP2}=V_{PP}$	I _{PP2}		100	mA
VPP Supply Current during Programing Inhibit and Verify	$\overline{CSL}=\overline{CSH}=V_{IH}$	I _{PP3}		10	mA
VCC Supply Current during Programing and Verify		I _{CC1}		100	mA
Input High Voltage		V _{IH}	2.4	V _{CC} +0.3	V
Input Low Voltage		V _{IL}	-0.1	0.6	V
Output High Voltage	V _{OH} =-1.0mA	V _{OH}	2.4		V
Output Low Voltage	V _{OL} =2.1mA	V _{OL}		0.45	V

Note: *₁ VCC must be applied either coincidentally or before VPP, and removed either coincidentally or after VPP.
 *₂ VPP must not be greater than 13.5 volts including overshoot. Permanent device damage may occur if the card is taken out or put into programmer remaining VPP=12.5 volts.

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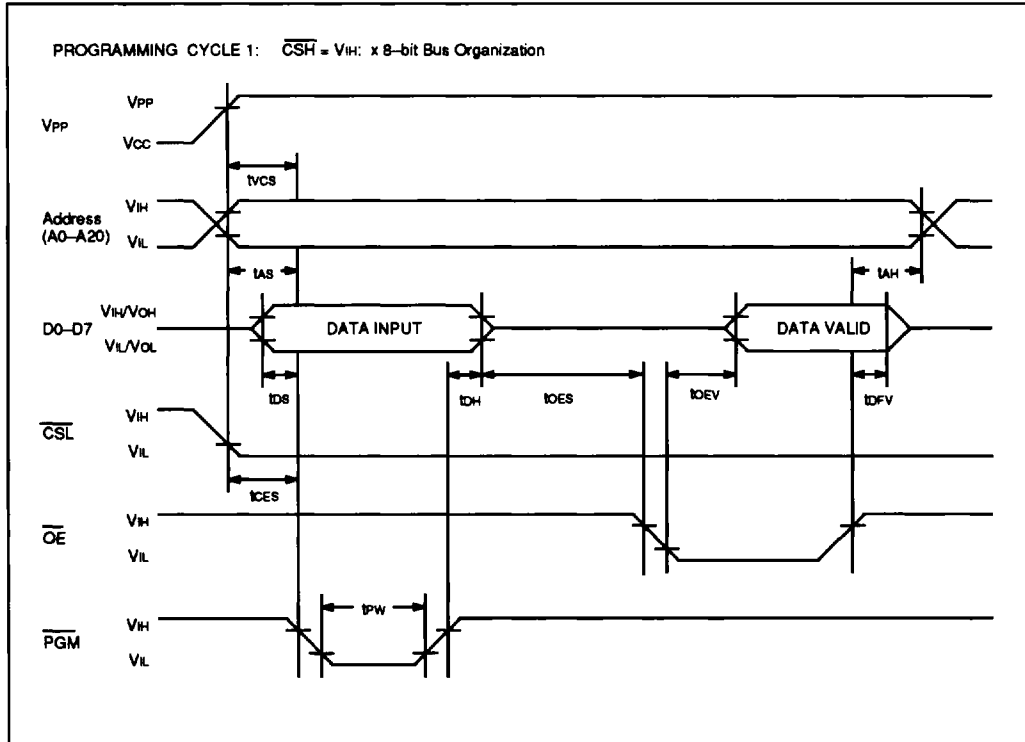
PROGRAMMING INFORMATION (Continued)

AC CHARACTERISTICS (TA=25°C, VCC=6V±0.25V, VPP=12.5V±0.5V)

Parameter	Symbol	Min	Typ	Max	Unit
Address Setup Time	tAS	2			μs
Data Setup Time	tDS	2			μs
Chip Enable Setup Time	tCES	2			μs
Output Enable Setup Time	tOES	2			μs
Vcc Setup Time	tVCS	2			μs
Programming Pulse Width	tPW	0.475	0.5	0.525	ms
Additional Programming Pulse Width	tAPW	1.4		39.4	ms
Programming Pulse Number	N	1		25	Times
Data Hold Time	tDH	2			μs
Address Hold Time	tAH	2			μs
Output Enable to Data Valid	tOEV			500	ns
Output Disable to Output Float Delay	tDFV			150	ns

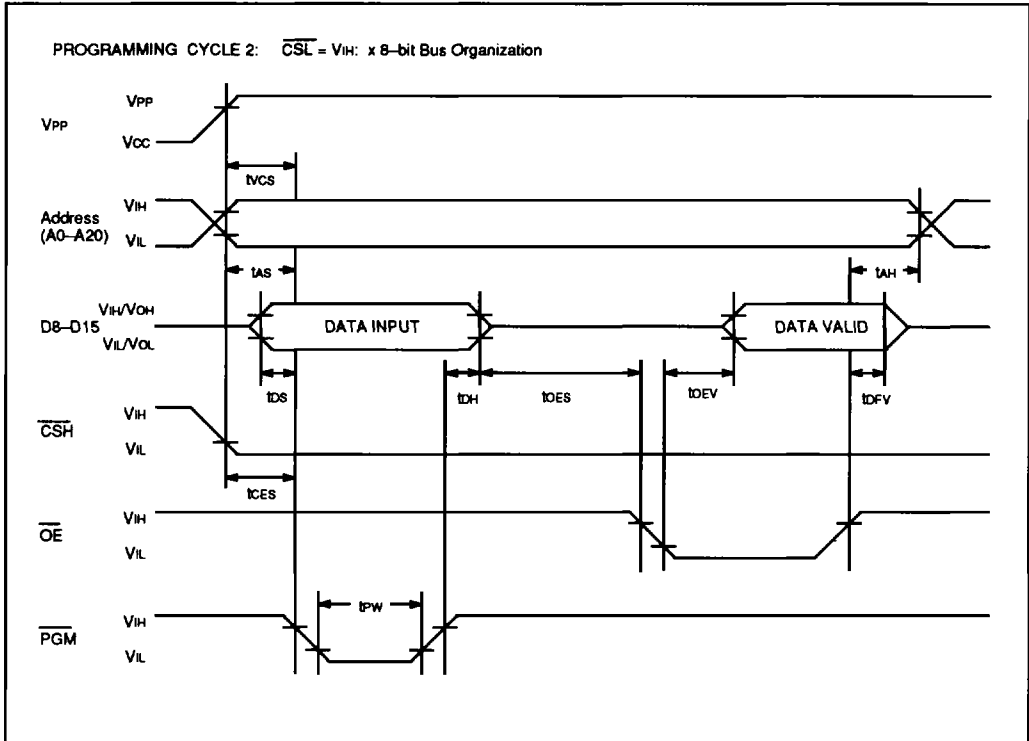
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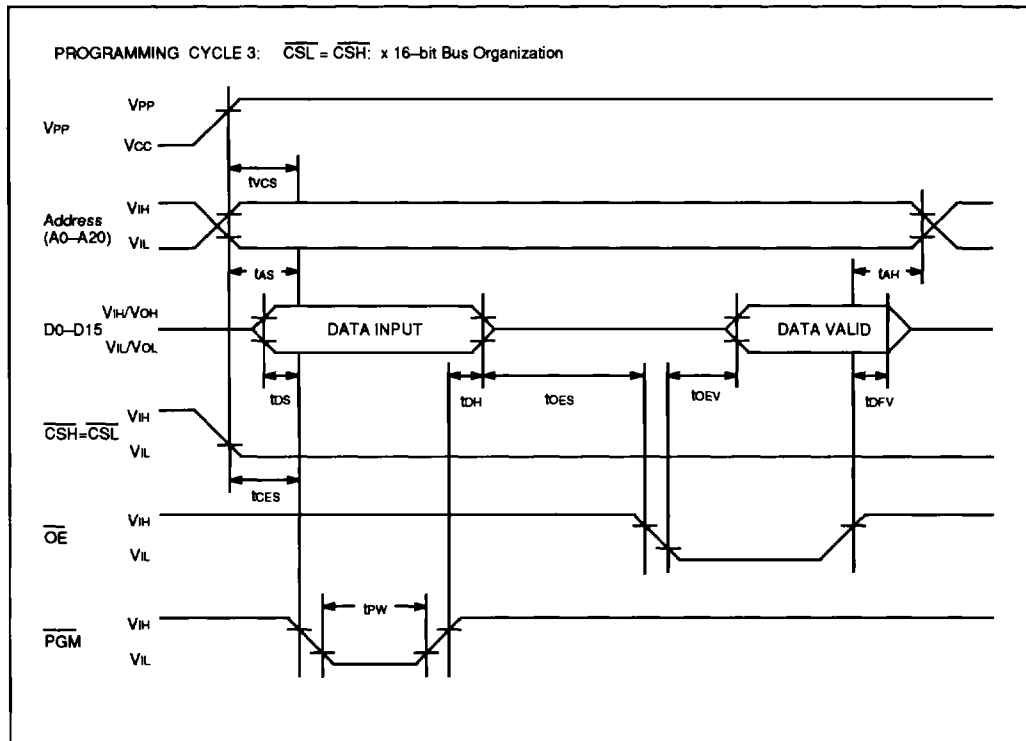


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PROGRAMMING INFORMATION (Continued)

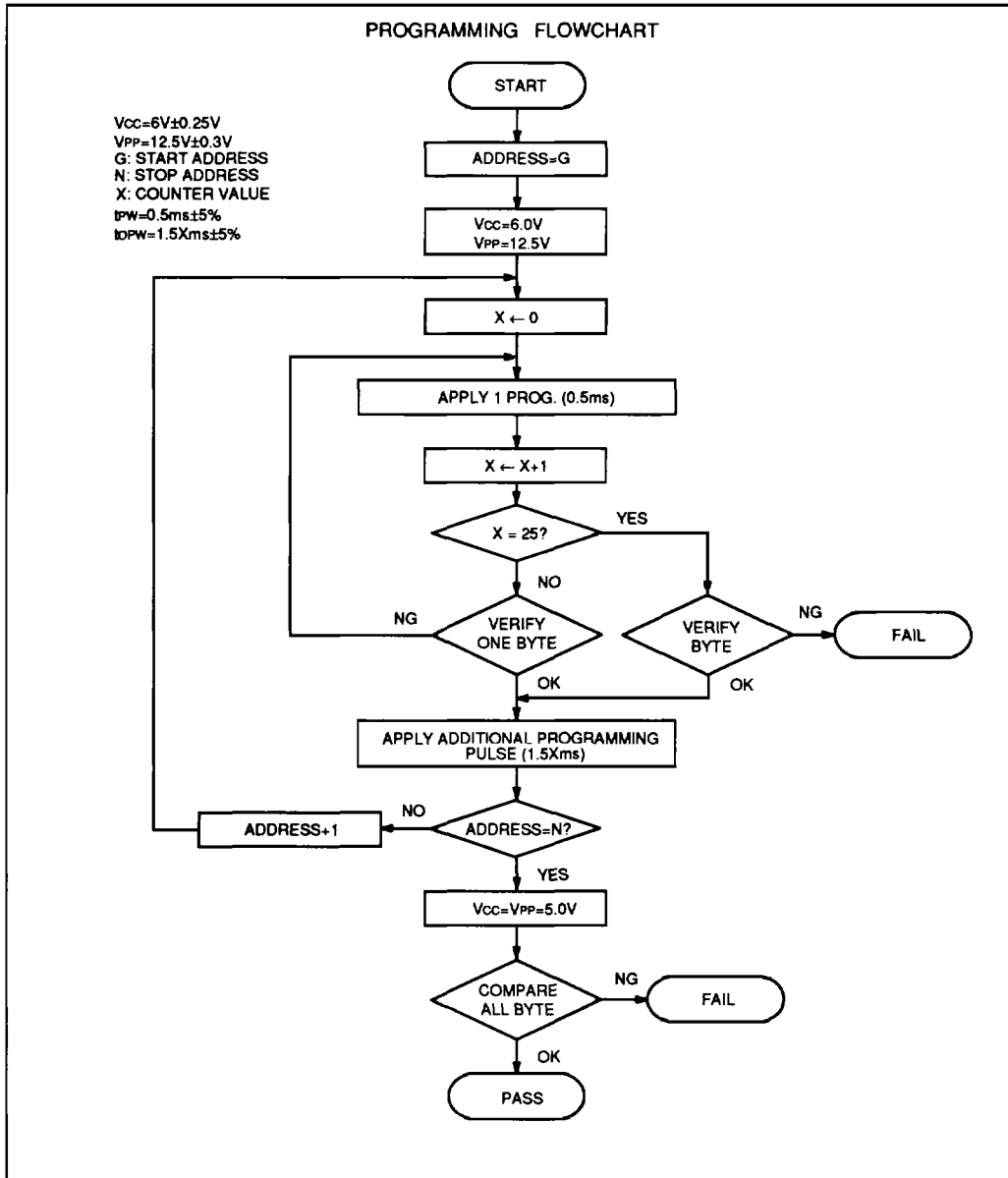


PROGRAMMING INFORMATION (Continued)



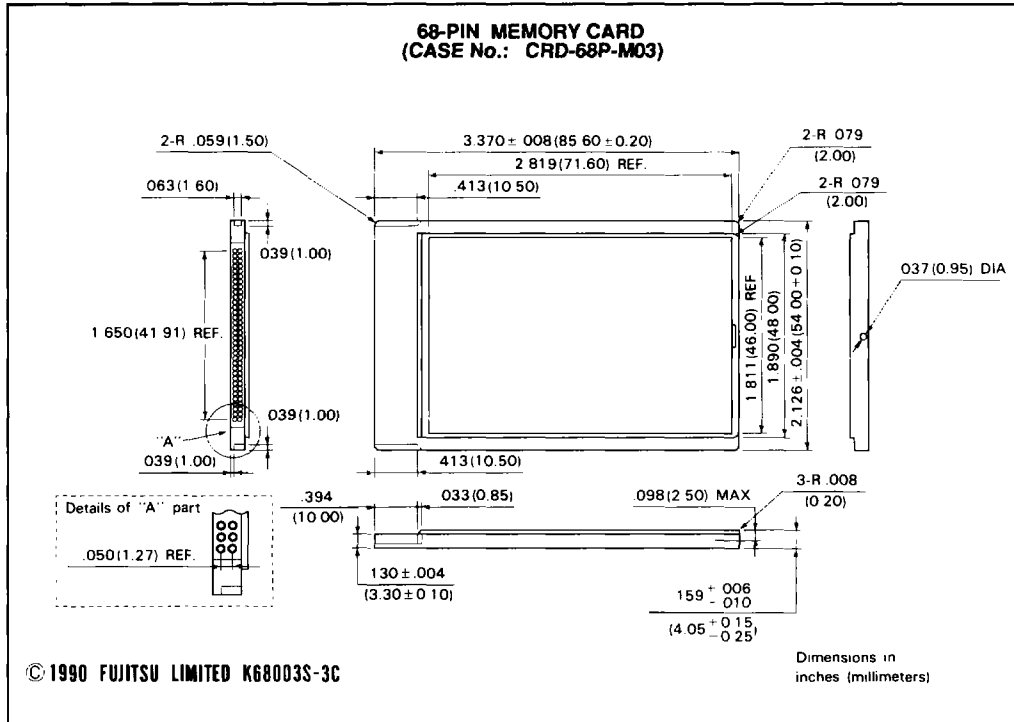
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PROGRAMMING INFORMATION (Continued)



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PACKAGE DIMENSIONS



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